Listing of the Claims

1. (Original) A method for forming a gate dielectric layer comprising:

providing a semiconductor substrate;

thermally oxidizing the semiconductor substrate within a thermal oxidizing atmosphere comprising a halogen getter material to form a gate dielectric layer upon a thermally oxidized semiconductor substrate.

2. (Original) The method of claim 1 wherein the semiconductor substrate is a silicon semiconductor substrate.

3. (Original) The method of claim 1 wherein the semiconductor substrate is a silicon-germanium alloy semiconductor substrate.

4. (Original) The method of claim 1 wherein the gate dielectric layer is formed from a non-nitrided silicon oxide material.

5. (Original) The method of claim 1 wherein the halogen getter material is a chlorine halogen getter material.

6. (Original) The method of claim 5 wherein the chlorine halogen getter material is selected from the group consisting of chlorine, hydrogen chloride, and one to three carbon atom chlorocarbons and hydrochlorocarbons.

7. (Original) The method of claim 1 wherein the thermal oxidizing atmosphere is selected from the group consisting of wet thermal oxidizing atmospheres and dry thermal oxidizing atmospheres.

8. (Original) A method for forming a gate dielectric layer comprising:

providing a semiconductor substrate;

thermally oxidizing the semiconductor substrate within a first thermal oxidizing atmosphere comprising a halogen getter material to form a first gate dielectric layer upon a once thermally oxidized semiconductor substrate; and

thermally oxidizing the once thermally oxidized semiconductor substrate within a second thermal oxidizing atmosphere not comprising a halogen getter material to form a second gate dielectric layer over a twice thermally oxidized semiconductor substrate.

9. (Original) The method of claim 8 wherein the semiconductor substrate is a silicon semiconductor substrate.

10. (Original) The method of claim 8 wherein the semiconductor substrate is a silicon-germanium alloy semiconductor substrate.

11. (Original) The method of claim 8 wherein the first gate dielectric layer is formed from a non-nitrided silicon oxide material.

12. (Original) The method of claim 8 wherein the second gate dielectric layer is formed from a nitrided silicon oxide material.

13. (Original) The method of claim 8 wherein the halogen getter material is a chlorine halogen getter material.

14. (Original) The method of claim 13 wherein the chlorine halogen getter material is selected from the group consisting of chlorine, hydrogen chloride, and one to three carbon atom chlorocarbons and hydrochlorocarbons.

15. (Original) The method of claim 8 wherein the first thermal oxidizing atmosphere is selected from the group consisting of wet thermal oxidizing atmospheres and dry thermal oxidizing atmospheres.

16. (Original) The method of claim 8 wherein the second thermal oxidizing atmosphere is selected from the group consisting of wet thermal oxidizing atmospheres and dry thermal oxidizing atmospheres.

17. (Original) The method of claim 8 wherein the first gate dielectric layer is stripped from the once thermally oxidized semiconductor substrate prior to forming the second gate dielectric layer over the twice thermally oxidized semiconductor substrate.

18. (Original) The method of claim 8 wherein the second gate dielectric layer is formed upon the first gate dielectric layer which is formed upon the twice thermally oxidized semiconductor substrate.

19. - 20. (Cancelled)